

SiGe:C low-noise amplifier MMIC for GPS, GLONASS, Galileo and COMPASS

Rev. 6 — 18 January 2017

Product data sheet

1. General description

The BGU8009 is, also known as the GPS1201M, a Low-Noise Amplifier (LNA) for GNSS receiver applications, available in a small plastic 6-pin extremely thin leadless package. The BGU8009 requires one external matching inductor and one external decoupling capacitor.

The BGU8009 adapts itself to the changing environment resulting from co-habitation of different radio systems in modern cellular handsets. It has been designed for low power consumption and optimal performance when jamming signals from co-existing cellular transmitters are present. At low jamming power levels, it delivers 18 dB gain at a noise figure of 0.65 dB. During high jamming power levels, resulting for example from a cellular transmit burst, it temporarily increases its bias current to improve sensitivity.

2. Features and benefits

- Covers full GNSS L1 band, from 1559 MHz to 1610 MHz
- Noise figure = 0.65 dB
- Gain 18 dB
- High input 1 dB compression point of -7 dBm
- High out of band IP3_i of 6 dBm
- Supply voltage 1.5 V to 3.1 V
- Optimized performance at very low supply current of 4.2 mA
- Power-down mode current consumption < 1 μA</p>
- Integrated temperature stabilized bias for easy design
- Requires only one input matching inductor and one supply decoupling capacitor
- Input and output DC decoupled
- ESD protection on all pins (HBM > 2 kV)
- Integrated matching for the output
- Available in a 6-pins leadless package 1.1 mm × 0.9 mm × 0.47 mm; 0.4 mm pitch: SOT1230
- 180 GHz transit frequency SiGe:C technology
- Moisture sensitivity level 1



3. Applications

- Smart phones
- Feature phones
- Tablets
- Digital still cameras
- Digital video cameras
- RF front-end modules
- Complete GNSS modules
- Personal health applications

4. Quick reference data

Table 1.Quick reference data

 $f = 1575 \text{ MHz}; V_{CC} = 2.85 \text{ V}; P_i < -40 \text{ dBm}; T_{amb} = 25 \text{ °C}; input matched to 50 \Omega using a 5.6 nH inductor, see <u>Figure 34</u>; unless otherwise specified.$

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{CC}	supply voltage			1.5	-	3.1	V
I _{CC}	supply current	$V_{I(ENABLE)} \ge 0.8 V$					
		P _i < -40 dBm		2.6	4.4	6.5	mA
		$P_i = -20 \text{ dBm}$		-	9	-	mA
G _p	power gain	P _i < -40 dBm		16	17.8	20	dB
		$P_i = -20 \text{ dBm}$		-	20.0	-	dB
NF	noise figure	P _i < -40 dBm	[1]	-	0.65	1.2	dB
		P _i < -40 dBm	[2]	-	0.70	1.25	dB
P _{i(1dB)}	input power at 1 dB gain compression	V _{CC} = 1.8 V		-	-10	-	dBm
		V _{CC} = 2.85 V		-12.5	-7	-	dBm
IP3 _i	input third-order intercept point	V _{CC} = 1.8 V	[3]	-	3	-	dBm
		V _{CC} = 2.85 V	[3]	-	6	-	dBm

[1] PCB losses are subtracted.

[2] Including PCB losses.

[3] $f_1 = 1713$ MHz; $f_2 = 1851$ MHz; $P_i = -20$ dBm per carrier.

5. Ordering information

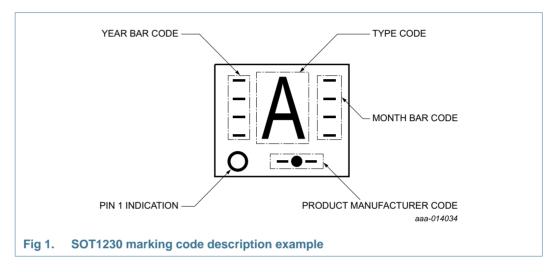
Table 2.Ordering information

Type number	Package	Package						
	Name	Description	Version					
BGU8009	XSON6	plastic very thin small outline package; no leads; 6 terminals; body 1.1 \times 0.9 \times 0.47 mm	SOT1230					
OM7820	EVB	BGU8009 evaluation board, MMIC only	-					
OM7824	EVB	BGU8009 evaluation board, front-end EVB	-					

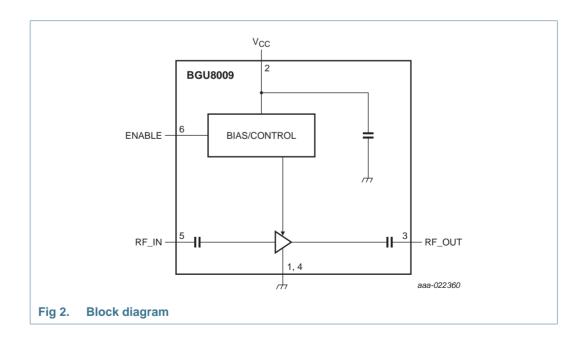
6. Marking

Table 3. Marking codes	
Type number	Marking code
BGU8009	A

6.1 Marking code description

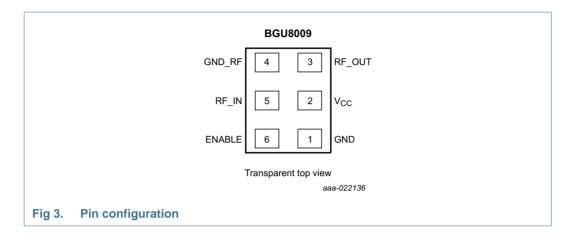


7. Block diagram



8. Pinning information

8.1 Pinning



8.2 Pin description

Table 4. Pin description

Symbol	Pin	Description
GND	1	ground
V _{CC}	2	supply voltage
RF_OUT	3	RF output
GND_RF	4	RF ground
RF_IN	5	RF input
ENABLE	6	enable

9. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Absolute Maximum Ratings are given as Limiting Values of stress conditions during operation, that must not be exceeded under the worst probable conditions.

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage	[1]	-0.5	+5.0	V
V _{I(ENABLE)}	input voltage on pin ENABLE	$V_{I(ENABLE)} < V_{CC} + 0.6 V$ [1][2]	-0.5	+5.0	V
V _{I(RF_IN)}	input voltage on pin RF_IN	DC, V _{I(RF_IN)} < V _{CC} + 0.6 V [1][2][3]	-0.5	+5.0	V
V _{I(RF_OUT)}	input voltage on pin RF_OUT	DC, $V_{I(RF_{OUT})} < V_{CC} + 0.6 V$ [1][2][3]	-0.5	+5.0	V
Pi	input power	1575 MHz [1]	-	10	dBm
P _{tot}	total power dissipation	$T_{sp} \le 130 \ ^{\circ}C$	-	55	mW
T _{stg}	storage temperature		-65	+150	°C

Table 5. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Absolute Maximum Ratings are given as Limiting Values of stress conditions during operation, that must not be exceeded under the worst probable conditions.

Symbol	Parameter	Conditions	Min	Max	Unit
Tj	junction temperature		-	150	°C
V _{ESD}	electrostatic discharge voltage	Human Body Model (HBM) according to JEDEC standard JS-001-2010	-	±2	kV
		Charged Device Model (CDM) according to JEDEC standard JESD22-C101C	-	±1	kV

[1] Stressed with pulses of 200 ms in duration, with application circuit as in Figure 34.

[2] Warning: due to internal ESD diode protection, the applied DC voltage shall not exceed V_{CC} + 0.6 V and shall not exceed 5.0 V to avoid excess current.

[3] The RF input and RF output are AC coupled through internal DC blocking capacitors.

10. Recommended operating conditions

Table 6. Operating conditions

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CC}	supply voltage		1.5	-	3.1	V
T _{amb}	ambient temperature		-40	+25	+85	°C
V _{I(ENABLE)}	input voltage on pin ENABLE	OFF state	-	-	0.3	V
		ON state	0.8	-	-	V

11. Thermal characteristics

Table 7.Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point		225	K/W

12. Characteristics

Table 8.Characteristics at V_{CC} = 1.8 V

 $f = 1575 \text{ MHz}, V_{CC} = 1.8 \text{ V}, V_{I(ENABLE)} >= 0.8 \text{ V}, P_i < -40 \text{ dBm} \text{ and } T_{amb} = 25 \text{ °C}.$ Input matched to 50 Ω using a 5.6 nH inductor, see Figure 34, unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CC}	supply current	$V_{I(ENABLE)} \ge 0.8 V$				
		$P_i < -40 \text{ dBm}$	2.3	4.2	6.2	mA
		$P_i = -20 \text{ dBm}$	-	9	-	mA
		$V_{I(ENABLE)} \le 0.3 V$	-	-	1	μA
G _p	power gain	no jammer	16	17.6	20	dB
	P _{jam} =	$P_{jam} = -20 \text{ dBm}; f_{jam} = 850 \text{ MHz}$	-	19.8	-	dB
		$P_{jam} = -20 \text{ dBm}; f_{jam} = 1850 \text{ MHz}$	-	20.0	-	dB
RL _{in}	input return loss	$P_i < -40 \text{ dBm}$	-	9	-	dB
		$P_i = -20 \text{ dBm}$	-	11	-	dB

SiGe:C low-noise amplifier MMIC for GPS, GLONASS, Galileo and COMPASS

Table 8. Characteristics at V_{CC} = 1.8 V ...continued

 $f = 1575 \text{ MHz}, V_{CC} = 1.8 \text{ V}, V_{I(ENABLE)} >= 0.8 \text{ V}, P_i < -40 \text{ dBm} \text{ and } T_{amb} = 25 \text{ }^{\circ}\text{C}.$ Input matched to 50 Ω using a 5.6 nH inductor, see Figure 34, unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
RL _{out}	output return loss	$P_i < -40 \text{ dBm}$		-	15	-	dB
		$P_i = -20 \text{ dBm}$		-	15	-	dB
ISL	isolation			-	37	-	dB
NF	noise figure	$P_i = -40 \text{ dBm}; \text{ no jammer}$	[1][2]	-	0.65	1.2	dB
		P _i = -40 dBm; no jammer	[2][3]	-	0.70	1.25	dB
		$P_{jam} = -20 \text{ dBm}; f_{jam} = 850 \text{ MHz}$	[3]	-	0.9	-	dB
		$P_{jam} = -20 \text{ dBm}; f_{jam} = 1850 \text{ MHz}$	[3]	-	1.2	-	dB
P _{i(1dB)}	input power at 1 dB gain compression			-	-10	-	dB m
IP3 _i	input third-order intercept point		[4]	-	3	-	dB m
			[5]	-	3	-	dB m
t _{on}	turn-on time	time from $V_{I(\text{ENABLE})}$ ON to 90 % of the gain		-	-	2	μS
t _{off}	turn-off time	time from $V_{I(\text{ENABLE})}$ OFF to 10 % of the gain		-	-	1	μS

[1] PCB losses are subtracted.

[2] Guaranteed by device design; not tested in production.

- [3] Including PCB losses.
- [4] $f_1 = 1713$ MHz; $f_2 = 1851$ MHz, $P_i = -20$ dBm per carrier.

 $\label{eq:hardenergy} [5] \quad f_1 = 1713 \; MHz; \, f_2 = 1851 \; MHz, \, P_{i(1)} = -20 \; dBm, \, P_{i(2)} = -65 \; dBm.$

Table 9. Characteristics at V_{cc} = 2.85 V

 $f = 1575 \text{ MHz}, V_{CC} = 2.85 \text{ V}, V_{I(ENABLE)} >= 0.8 \text{ V}, P_i < -40 \text{ dBm} \text{ and } T_{amb} = 25 \text{ }^{\circ}\text{C}.$ Input matched to 50 Ω using a 5.6 nH inductor, see <u>Figure 34</u>, unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
I _{CC}	supply current	$V_{I(ENABLE)} \ge 0.8 V$				
		P _i < -40 dBm	2.6	4.4	6.5	mA
		$P_i = -20 \text{ dBm}$	-	9	-	mA
		$V_{I(ENABLE)} \le 0.3 V$	-	-	1	μA
G _p	power gain	no jammer	16	17.8	20	dB
		$P_{jam} = -20 \text{ dBm}; f_{jam} = 850 \text{ MHz}$	-	20.0	-	dB
		$P_{jam} = -20 \text{ dBm}; f_{jam} = 1850 \text{ MHz}$	-	20.2	-	dB
RL _{in}	input return loss	P _i < -40 dBm	-	9	-	dB
		$P_i = -20 \text{ dBm}$	-	11	-	dB
RL _{out}	output return loss	P _i < -40 dBm	-	15	-	dB
		$P_i = -20 \text{ dBm}$	-	15	-	dB
ISL	isolation		-	37	-	dB

SiGe:C low-noise amplifier MMIC for GPS, GLONASS, Galileo and COMPASS

Table 9. Characteristics at V_{cc} = 2.85 V ...continued

 $f = 1575 \text{ MHz}, V_{CC} = 2.85 \text{ V}, V_{I(ENABLE)} >= 0.8 \text{ V}, P_i < -40 \text{ dBm} \text{ and } T_{amb} = 25 \text{ °C}.$ Input matched to 50 Ω using a 5.6 nH inductor, see Figure 34, unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
NF	noise figure	$P_i = -40 \text{ dBm}; \text{ no jammer}$	[1][2]	-	0.65	1.2	dB
		$P_i = -40 \text{ dBm}; \text{ no jammer}$	[2][3]	-	0.70	1.25	dB
		$P_{jam} = -20 \text{ dBm}; f_{jam} = 850 \text{ MHz}$	[3]	-	0.9	-	dB
		$P_{jam} = -20 \text{ dBm}; f_{jam} = 1850 \text{ MHz}$	[3]	-	1.2	-	dB
P _{i(1dB)}	input power at 1 dB gain compression		[2]	-12.5	-7	-	dBm
IP3 _i	input third-order intercept point		[2][4]	0	6	-	dBm
			[2][5]	0	6	-	dBm
t _{on}	turn-on time	time from $V_{I(ENABLE)}$ ON to 90 % of the gain		-	-	2	μs
t _{off}	turn-off time	time from $V_{I(\text{ENABLE})}$ OFF to 10 % of the gain		-	-	1	μS

[1] PCB losses are subtracted.

[2] Guaranteed by device design; not tested in production.

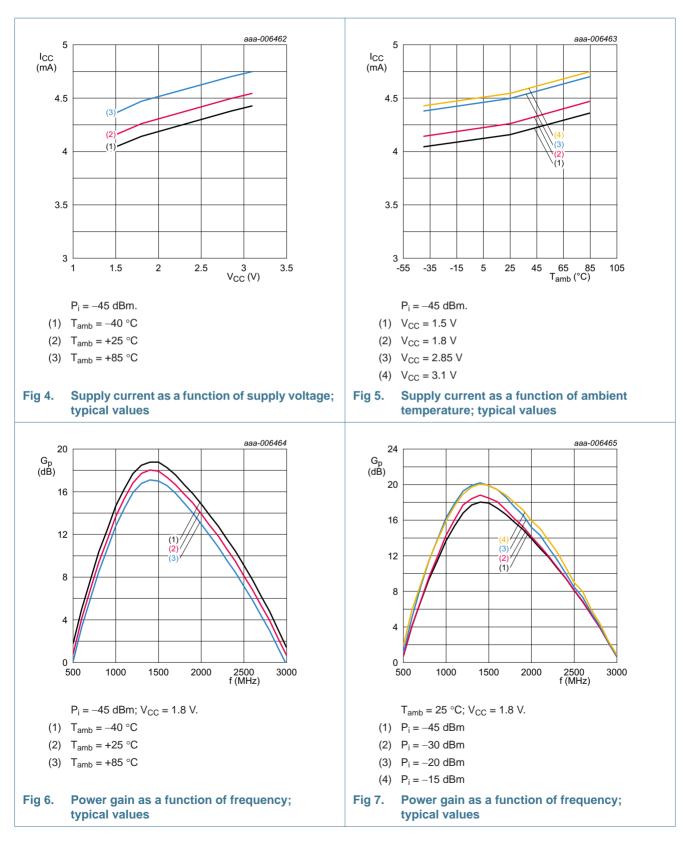
[3] Including PCB losses.

[4] $f_1 = 1713$ MHz; $f_2 = 1851$ MHz, $P_i = -20$ dBm per carrier.

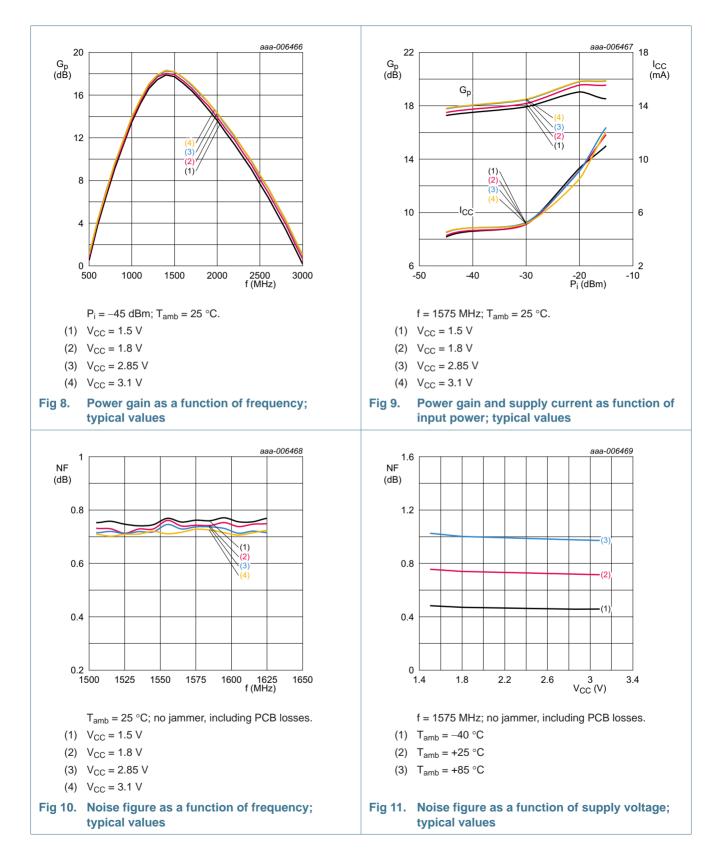
[5] $f_1 = 1713 \text{ MHz}; f_2 = 1851 \text{ MHz}, P_{i(1)} = -20 \text{ dBm}, P_{i(2)} = -65 \text{ dBm}.$

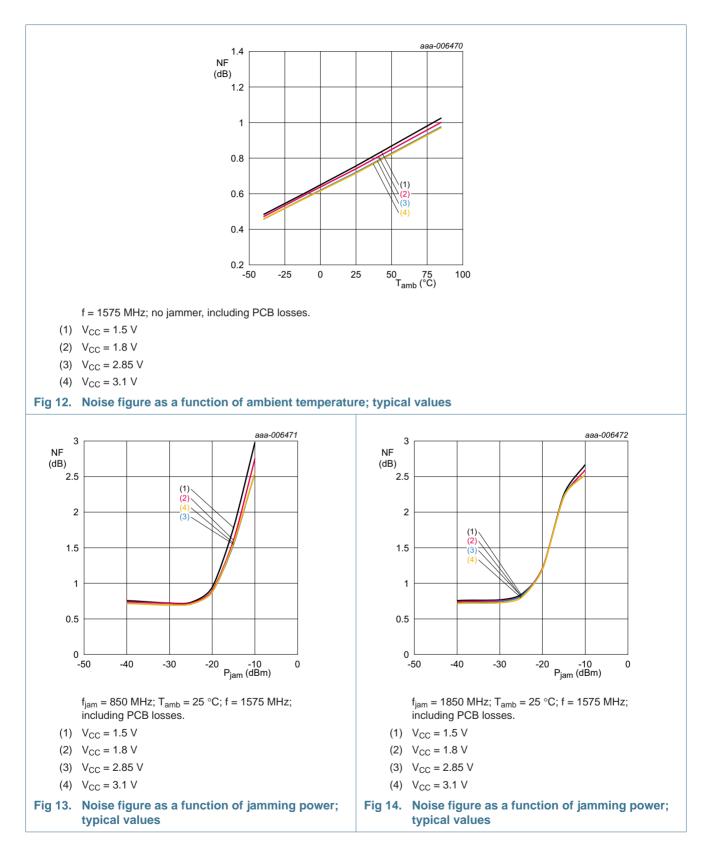
SiGe:C low-noise amplifier MMIC for GPS, GLONASS, Galileo and COMPASS

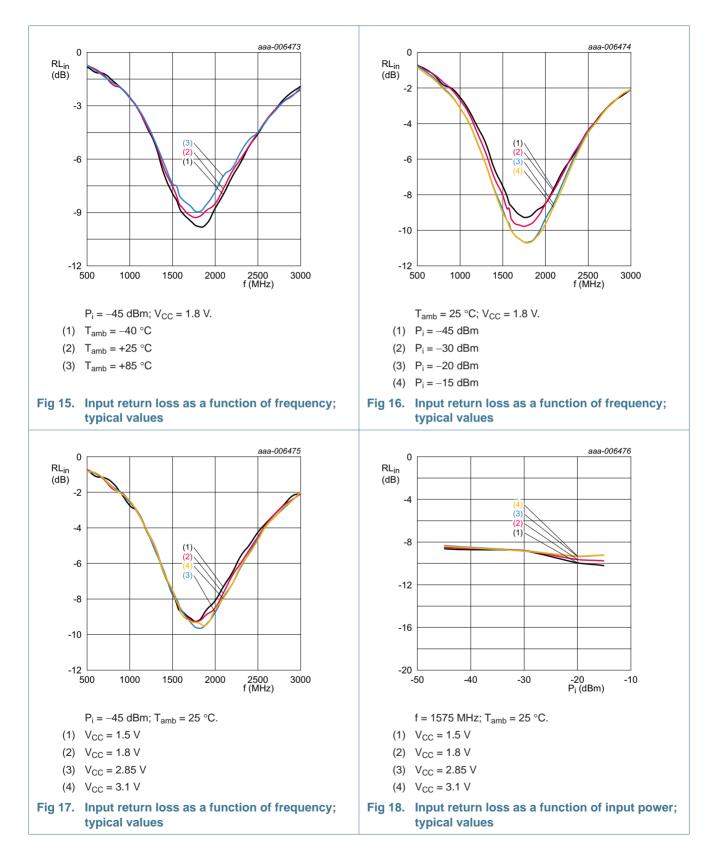
13. Graphs

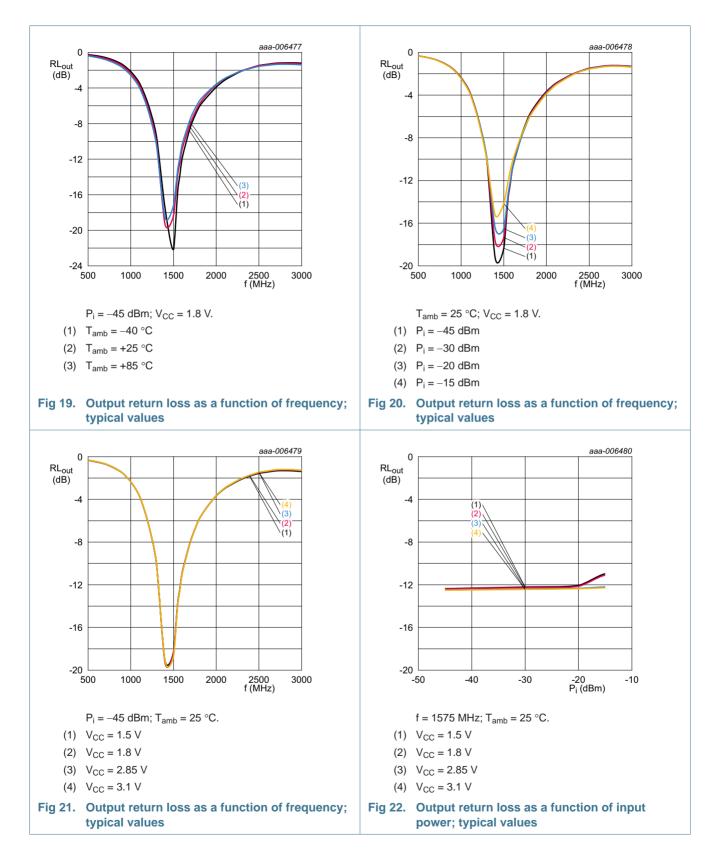


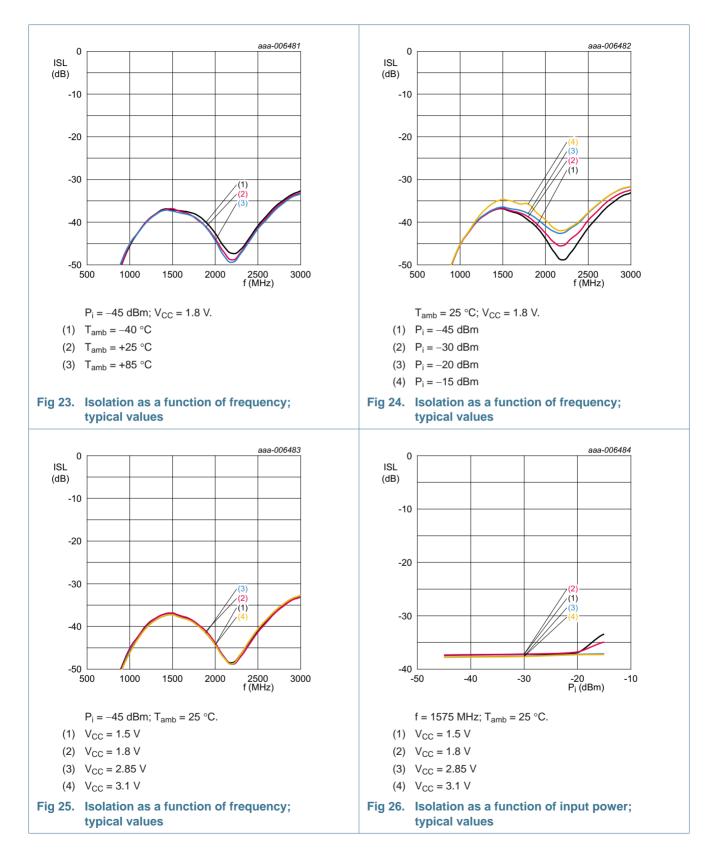
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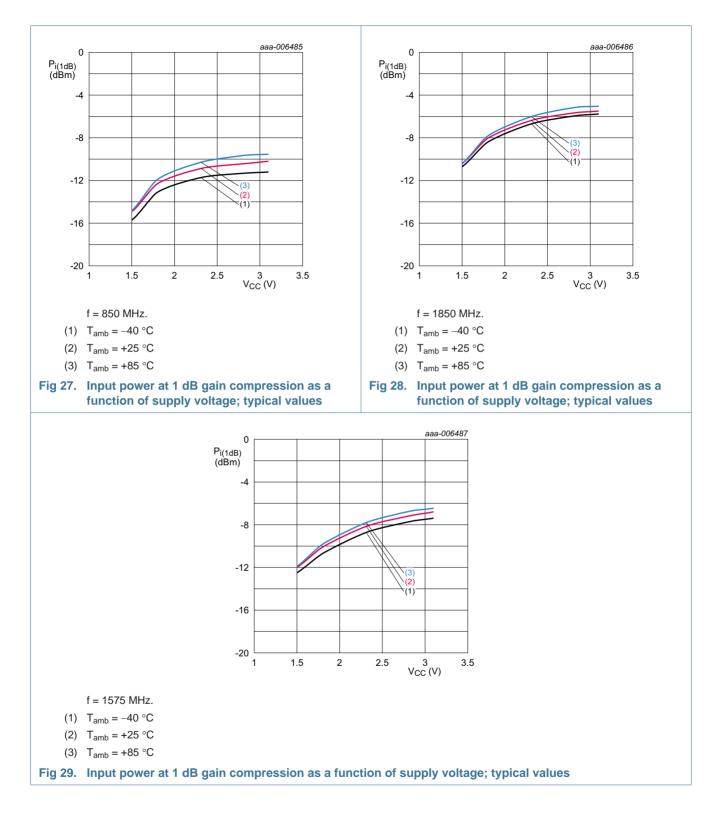


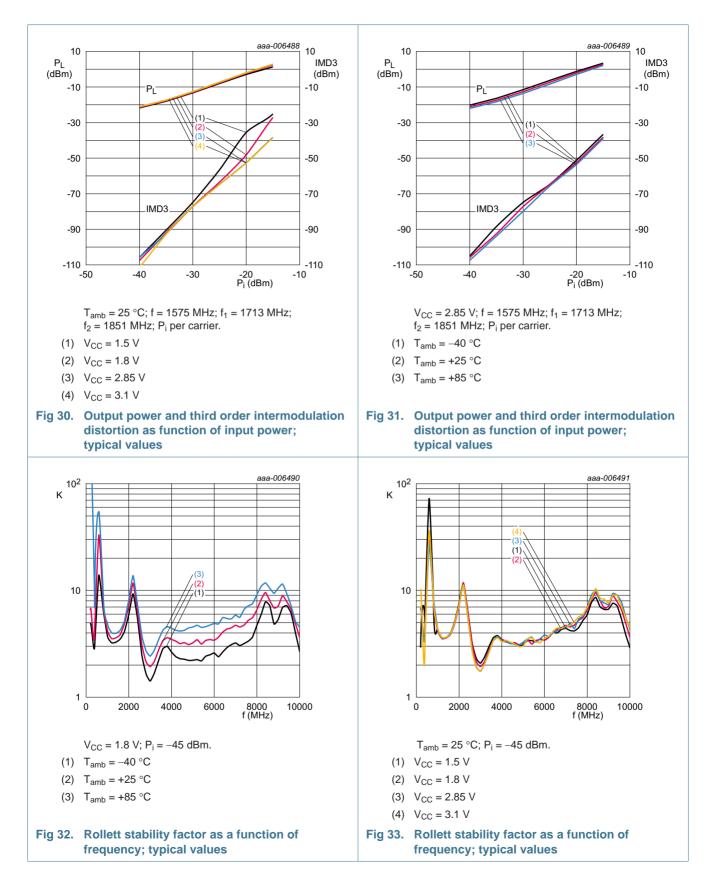












14. Application information

14.1 GNSS LNA

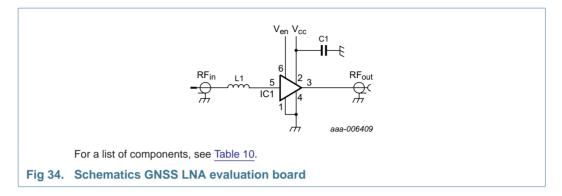


Table 10. List of components for Figure 34

Component	Description	Value	Remarks
C1	decoupling capacitor	1 nF	
IC1	BGU8009	-	NXP Semiconductors
L1	high-quality matching inductor	5.6 nH	Murata LQW15A

See application note AN11288 for details.

BGU8009 SiGe:C low-noise amplifier MMIC for GPS, GLONASS, Galileo and COMPASS

15. Package outline

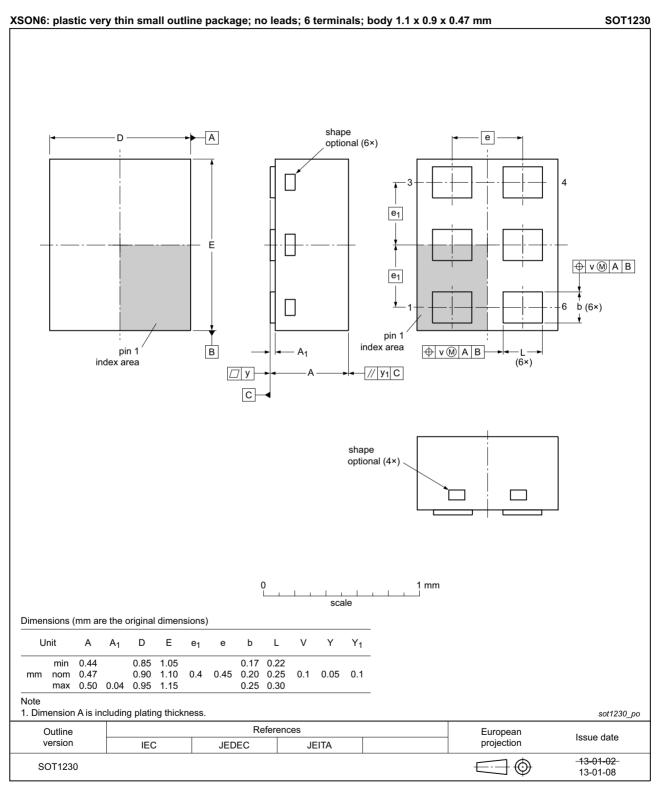


Fig 35. Package outline SOT1230 (XSON6)

16. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

17. Abbreviations

Table 11. Abbreviations

Acronym	Description
GLONASS	Global Navigation Satellite System
GNSS	Global Navigation Satellite System
GPS	Global Positioning System
НВМ	Human Body Model
MMIC	Monolithic Microwave Integrated Circuit
РСВ	Printed-Circuit Board
SiGe:C	Silicon Germanium Carbon

18. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BGU8009 v.6	20170118	Product data sheet	-	BGU8009 v.5
Modifications:	<u>Section 1</u> : added GPS1201M according to our new naming convention			
BGU8009 v.5	20160405	Product data sheet	-	BGU8009 v.4
Modifications:	updated Figure 2 "Block diagram" on page 3			
BGU8009 v.4	20160316	Product data sheet	-	BGU8009 v.3
Modifications:	updated Table 8 on page 5 and Table 9 on page 6			
BGU8009 v.3	20141001	Product data sheet	-	BGU8009 v.2
Modifications:	Section 6.1 on page 3: Section has been added.			
BGU8009 v.2	20130619	Product data sheet	-	BGU8009 v.1
BGU8009 v.1	20130201	Product data sheet	-	-

19. Legal information

19.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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21. Contents

1	General description 1
2	Features and benefits 1
3	Applications 2
4	Quick reference data 2
5	Ordering information 2
6	Marking 3
6.1	Marking code description 3
7	Block diagram 3
8	Pinning information 4
8.1	Pinning
8.2	Pin description 4
9	Limiting values 4
10	Recommended operating conditions 5
11	Thermal characteristics 5
12	Characteristics 5
13	Graphs
14	Application information 16
14.1	GNSS LNA 16
15	Package outline 17
16	Handling information 18
17	Abbreviations 18
18	Revision history 18
19	Legal information 19
19.1	Data sheet status 19
19.2	Definitions 19
19.3	Disclaimers
19.4	Trademarks
20	Contact information 20
21	Contents 21

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